#### **FEATURES**

- \* Low noise due to ultra soft fast recovery diode.
- \* High reliability, high durability diodes.
- \* Isolated heat sink (terminal to base).

#### ABSOLUTE MAXIMUM RATINGS (T<sub>C</sub>=25°C)

Item		Symbol	Unit	MDM1200E17D	
Repetitive Peak Reverse Voltage		$V_{RRM}$	V	1,700	
Forward Current	DC	I <sub>F</sub>	۸	1,200	
	1ms	I <sub>FM</sub>	A	2,400	
Junction Temperature		T <sub>vj op</sub>	°C	-40 ~ +125	
Storage Temperature		T <sub>stg</sub>	°C	-40 ~ +125	
Isolation Test Voltage	Terminals-base	V <sub>ISO</sub>	W	4,000(AC 1 minute)	
	Terminal 1-Terminal 2	V <sub>ISO T-T</sub>	V <sub>RMS</sub>	4,000(AC 1 minute)	
Screw Torque	Terminals (M8)	-	N⋅m	15 (1)	
	Mounting (M6)	-	IN·III	6 (2)	

Notes: (1) Recommended Value 15<sup>+0</sup><sub>-3</sub>N·m

(2) Recommended Value 5.5±0.5N·m

#### **ELECTRICAL CHARACTERISTICS**

ltem	Symbol	Unit	Min.	Тур.	Max.	Test Conditions
Repetitive Reverse Current	I <sub>RRM</sub>	mA	-	1.0	10.0	VAK=1,700V, T <sub>vj</sub> =125°C
Forward Voltage Drop	V <sub>F</sub>	V	1.8	2.1	2.5	I <sub>F</sub> =1200A, T <sub>vj</sub> =125°C
Reverse Recovery Time	t <sub>rr</sub>	μS	-	0.5	-	V <sub>CC</sub> =900V, I <sub>F</sub> =1,200A, L <sub>S</sub> =100nH R <sub>G</sub> =1.5Ω, C <sub>GF</sub> =120nF (3)
Reverse Recovery Loss	E <sub>rr(10%)</sub>	J/P	-	0.4	-	$R_{G}=1.5\Omega, C_{GE}=120nF$ (3) $T_{vi}=125^{\circ}C$

Notes: (3) Counter arm: MBN1200E17D  $V_{GE} = \pm 15V$ 

 $R_G$  and  $C_{GE}$  value are the test condition's value to define the switching characteristics not recommended value.

Please, determine the suitable R<sub>G</sub> and C<sub>GE</sub> value after the measurement of switching waveforms

(overshoot voltage, etc.) with appliance mounted.

#### PACKAGE CHARACTERISTICS

Item	Symbol	Unit	Min.	Тур.	Max.	Test Conditions
Terminal Resistance	RCE	mΩ	-	0.2	-	Tc=25°C, per arm
Stray inductance module	L <sub>SCE</sub>	nΗ	-	21	-	per arm
Thermal Impedance	R <sub>th(j-c)</sub>	K/W	-	-	0.033	Junction to case (par arm)
Contact Thermal Impedance	R <sub>th(c-f)</sub>	K/W	-	0.008	-	Case to fin (par module)

- \* Please contact our representatives at order.
- \* For improvement, specifications are subject to change without notice.
- \* For actual application, please confirm this spec sheet is the newest revision.



### **DEFINITION OF TEST CIRCUIT**

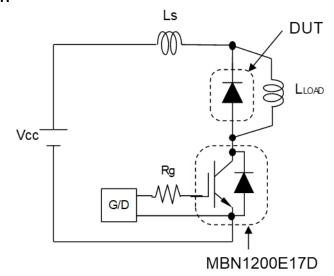


Fig.1 Switching test circuit

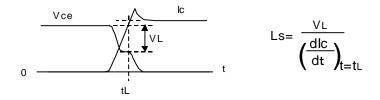


Fig.2 Definition of stray inductance

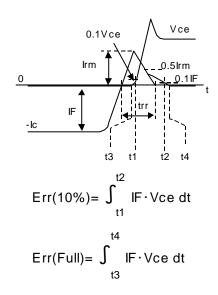
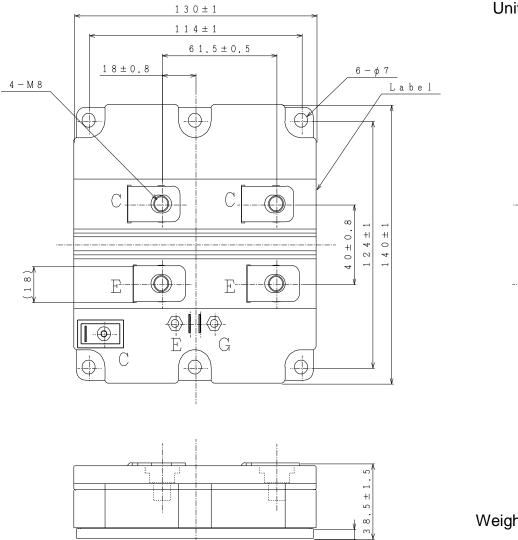
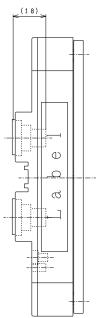


Fig.3 Definition of switching loss

### **OUTLINE DRAWING**

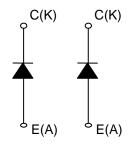


### Unit in mm

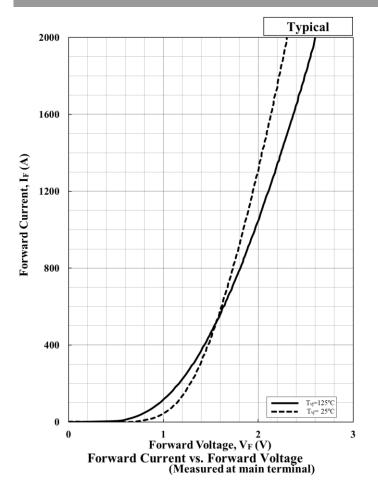


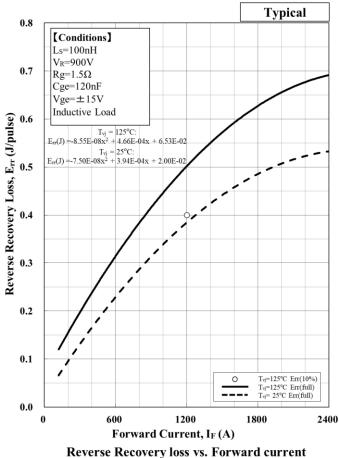
Weight: 900g

### **CIRCUIT DIAGRAM**





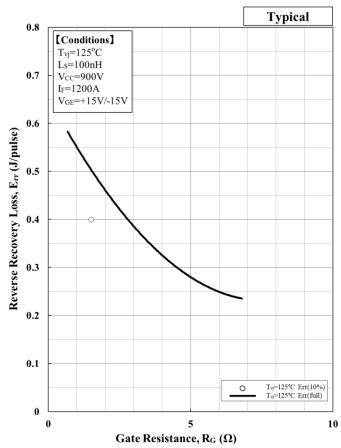




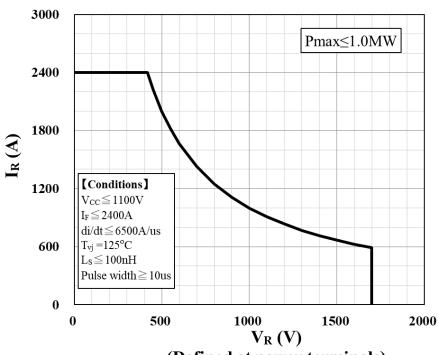
**Typical** 1.0 [Conditions]  $T_{vj}=125^{\circ}C$ L<sub>S</sub>=100nH V<sub>R</sub>=900V Rg=1.5Ω Cge=120nF 0.8  $Vge=\pm 15V$ Inductive Load Reverse Recovery time, t<sub>rr</sub> (us) 90 90 0.2 0.0 1200 1800 2400 Forward Current, I<sub>F</sub> (A)

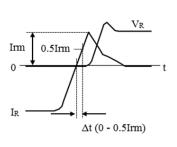
Reverse Recovery time vs. Forward Current





Reverse Recovery loss vs. Gate Resistance

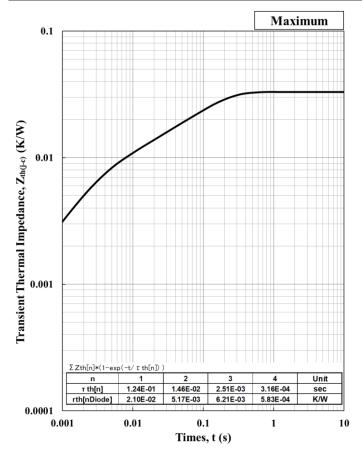




 $di/dt = \frac{0.5Irm}{\Delta t}$ 

Definition of Recovery di/dt

(Defined at power terminals)
Reverse Recovery Safe Operation Area (RRSOA)



**Transient Thermal Ipedance Curve** 

### **Material declaration**

Please note the following materials are contained in the product, in order to keep characteristic and reliability level.

Material	Contained part
Lead (Pb) and its compounds	Solder



## HITACHI POWER SEMICONDUCTORS

## Notices

- 1. Since mishandling of semiconductor devices may cause malfunctions, please be sure to read "Precautions for Safe Use and Notices" in the individual brochure before use.
- 2. When designing an electronic circuit using semiconductor devices, please do not exceed the absolute maximum rating specified for the device under any external fluctuations. And for pulse applications, please also do not exceed the "Safe Operating Area (SOA)".
- 3. Semiconductor devices may sometimes break down by accidental or unexpected surge voltage, so please be careful about the safety design such as redundant design and malfunction prevention design which don't cause the damage expand even if they break down.
- 4. In cases where extremely high reliability is required (such as use in nuclear power control, aerospace and aviation, traffic equipment, life-support-related medical equipment, fuel control equipment and various kinds of safety equipment), safety should be ensured by using semiconductor devices that feature assured safety or by means of users' fail-safe precautions or other arrangement. Or consult with Hitachi's sales department staff. (When semiconductor devices fail, as a result the semiconductor devices or wiring, wiring pattern may smoke, ignite, or the semiconductor devices themselves may burst.)
- 5. A semi-processed article is done now using solder which contains lead inside the semiconductor devices. There is possibility of the regulation substance depend on the applied models, so please check before using.
- 6. This specification is a material for component selection, which describes specifications of power semiconductor devices (hereinafter referred to as products), characteristic charts, and external dimension drawings.
- 7. The information given herein, including the specifications and dimensions, is subject to change without prior notice to improve product characteristics. Before ordering, purchasers are advised to contact with Hitachi power semiconductor sales department for the latest version of this data sheets.
- 8. For handling other than described in this manual, follow the handling instructions (IGBT-HI-00002).

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Hitachi power semiconductor home page address http://www.hitachi-power-semiconductor-device.co.jp/ http://www.hitachi-power-semiconductor-device.co.jp/en/



## HITACHI POWER SEMICONDUCTORS

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